

What is claimed is:

1. A method of making a monitoring pattern of a shallow trench isolation profile, comprising:

forming a first pattern on a substrate to monitor a depth of a first shallow trench isolation, and wherein the first pattern includes a plurality of unequally spaced active regions on the substrate; and

forming a second pattern on the substrate to measure electrical effects associated with a depth and a profile of a second shallow trench isolation, wherein the second pattern includes a plurality of equally spaced active regions on the substrate and a plurality of contact regions that electrically connect the equally spaced active regions.

2. The method as defined by claim 1, wherein the depth, the profile and the electrical effects are monitored according to density and size of the first and second patterns.

3. The method as defined by claim 1, wherein the depth and the profile are monitored using a single monitoring pattern.